

**20V N-Channel Enhancement Mode MOSFET****VDS= 20V**

RDS(ON), Vgs@ 4.5V, Ids@ 3.0A <70mΩ

RDS(ON), Vgs@ 2.5V, Ids@ 2.0A <80mΩ

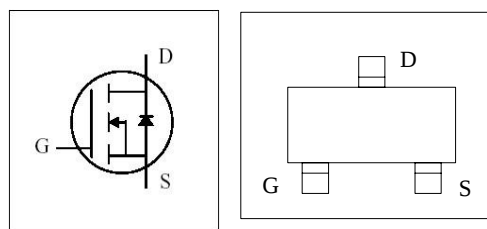
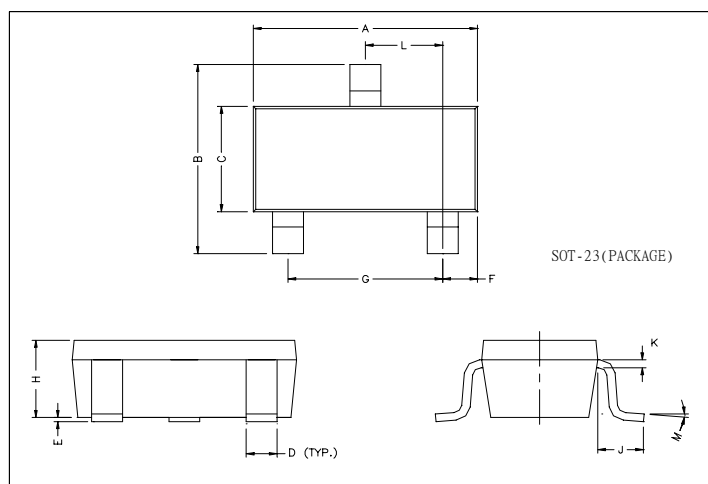
Features

Advanced trench process technology

High Density Cell Design For Ultra Low On-Resistance

High Power and Current handing capability

Ideal for Li ion battery pack applications

Package Dimensions

REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.10	G	1.90	REF.
B	2.40	2.80	H	1.00	1.30
C	1.40	1.60	K	0.10	0.20
D	0.35	0.50	J	0.40	-
E	0	0.10	L	0.85	1.15
F	0.45	0.55	M	0°	10°

Maximum Ratings and Thermal Characteristics (TA = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V _{DS}	20	V
Gate-Source Voltage		V _{GS}	± 12	
Continuous Drain Current		I _D	2.3	A
Pulsed Drain Current ¹⁾		I _{DM}	8	
Maximum Power Dissipation	TA = 25°C	P _D	1.25	W
	TA = 75°C		0.8	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150	°C
Junction-to-Ambient Thermal Resistance (PCB mounted) ²⁾		R _{θJA}	78	°C/W

Notes¹⁾ Pulse width limited by maximum junction temperature.²⁾ Surface Mounted on FR4 Board, t ≤ 5 sec.



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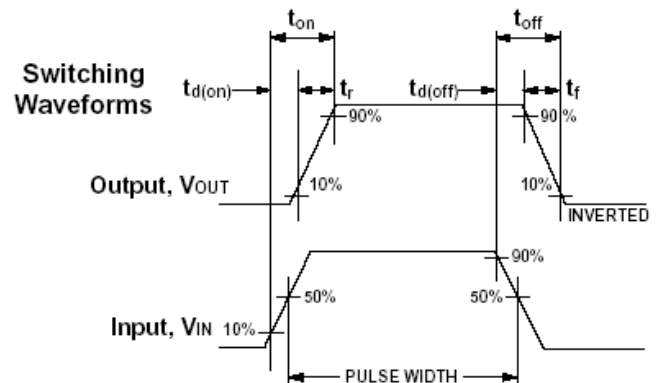
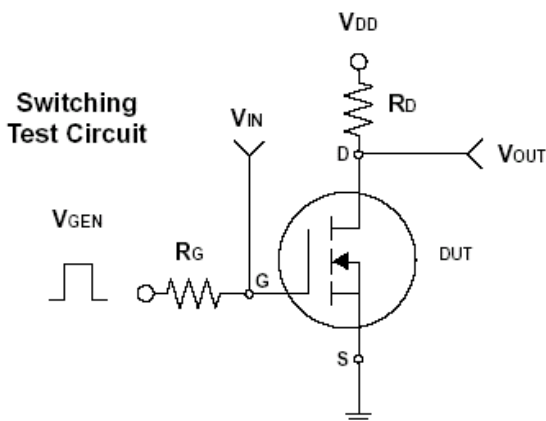
ELECTRICAL CHARACTERISTICS (TA = 25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Miax.	Unit
Static ³⁾						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D = 250uA	20			V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = 2.5V, I _D = 2.0A		70.0	80.0	mΩ
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = 4.5V, I _D = 3.0A		60.0	70.0	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D = 250uA	0.6	0.76		V
Zero Gate Voltage Drain Current 0	I _{DSS}	V _{DS} = 20V, V _{GS} = 0V			1	uA
Gate Body Leakage	I _{GSS}	V _{GS} = ± 12V, V _{DS} = 0V			±100	nA
Forward Transconductance	g _{fs}	V _{DS} = 5V, I _D = 4.2A		5	—	S
Dynamic ⁴⁾						
Total Gate Charge	Q _g	V _{DS} = 10V, I _D = 3.6A V _{GS} = 4.5V		5.4	10	nC
Gate-Source Charge	Q _{gs}			0.65		
Gate-Drain Charge	Q _{gd}			1.5		
Turn-On Delay Time	t _{d(on)}	V _{DD} = 10V, R _G = 6Ω I _D = 1A, V _{GS} = 4.5V RL = 5.5Ω		12	25	ns
Turn-On Rise Time	t _r			36	60	
Turn-Off Delay Time	t _{d(off)}			34	60	
Turn-Off Fall Time	t _f			10	25	
Input Capacitance	C _{iss}	V _{DS} = 10V, V _{GS} = 0V f = 1.0 MHz		340		pF
Output Capacitance	C _{oss}			115		
Reverse Transfer Capacitance	C _{rss}			33		
Source-Drain Diode						
Max. Diode Forward Current	I _S				1.6	A
Diode Forward Voltage	V _{SD}	I _S = 1.6A, V _{GS} = 0V			1.2	V

Notes

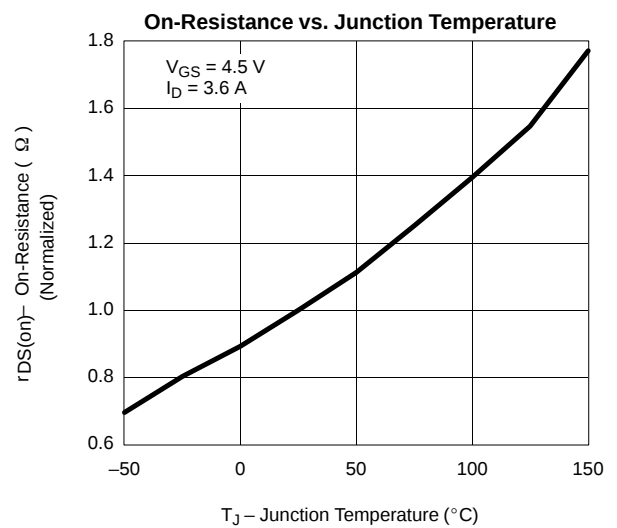
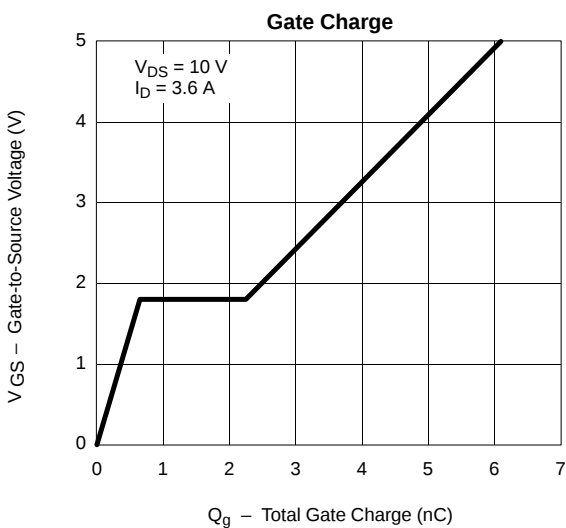
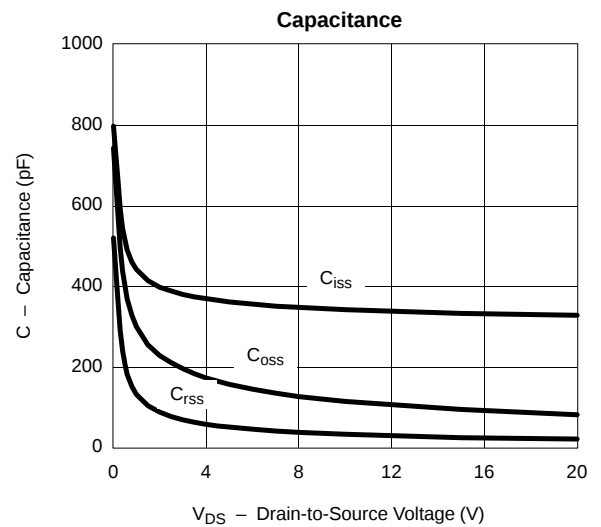
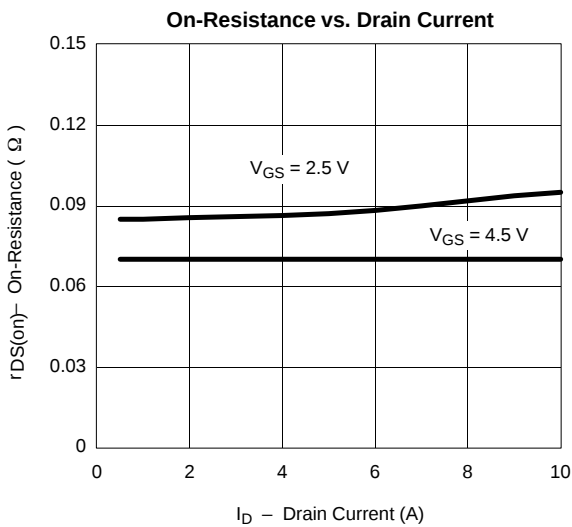
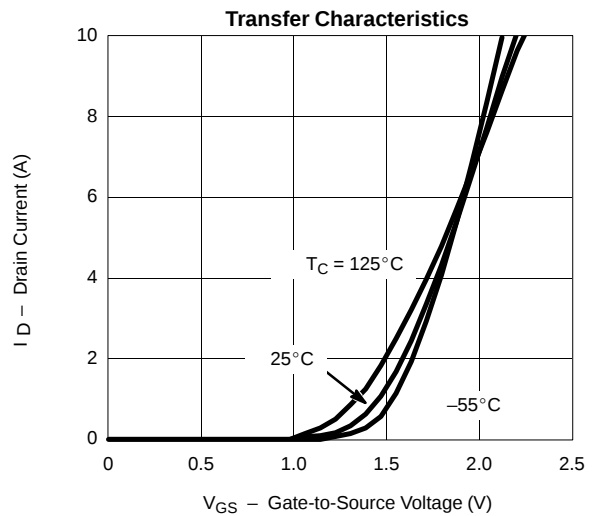
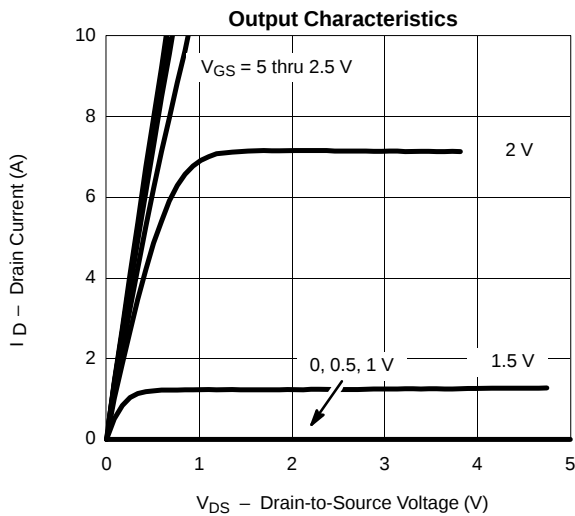
³⁾ Short duration test pulse used to minimize self-heating effect.

⁴⁾ Pulse test pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.





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